

N-Channel and P-Channel Enhancement-Mode MOSFET Pair

Features

- Integrated Gate-to-source Resistor
- Integrated Gate-to-source Zener Diode
- Low Threshold
- Low On-resistance
- Low Input Capacitance
- Fast Switching Speeds
- Free from Secondary Breakdown
- Low Input and Output Leakage
- Independent Electrically Isolated N-channel and P-channel

Applications

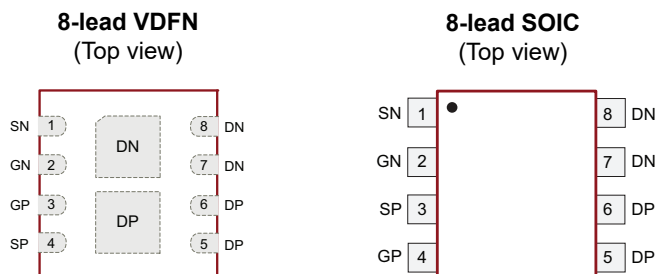
- High-voltage Pulsers
- Amplifiers
- Buffers
- Piezoelectric Transducer Drivers
- General Purpose Line Drivers
- Logic-level Interfaces

General Description

The TC6320 consists of high-voltage, low-threshold N-channel and P-channel MOSFETs in 8-lead VDFN and SOIC packages. Both MOSFETs have integrated gate-to-source resistors and gate-to-source Zener diode clamps which are desired for high-voltage pulser applications. It is a complimentary, high-speed, high-voltage, gate-clamped N-channel and P-channel MOSFET pair, which utilizes an advanced vertical DMOS structure and a well-proven silicon gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance and fast-switching speeds are desired.

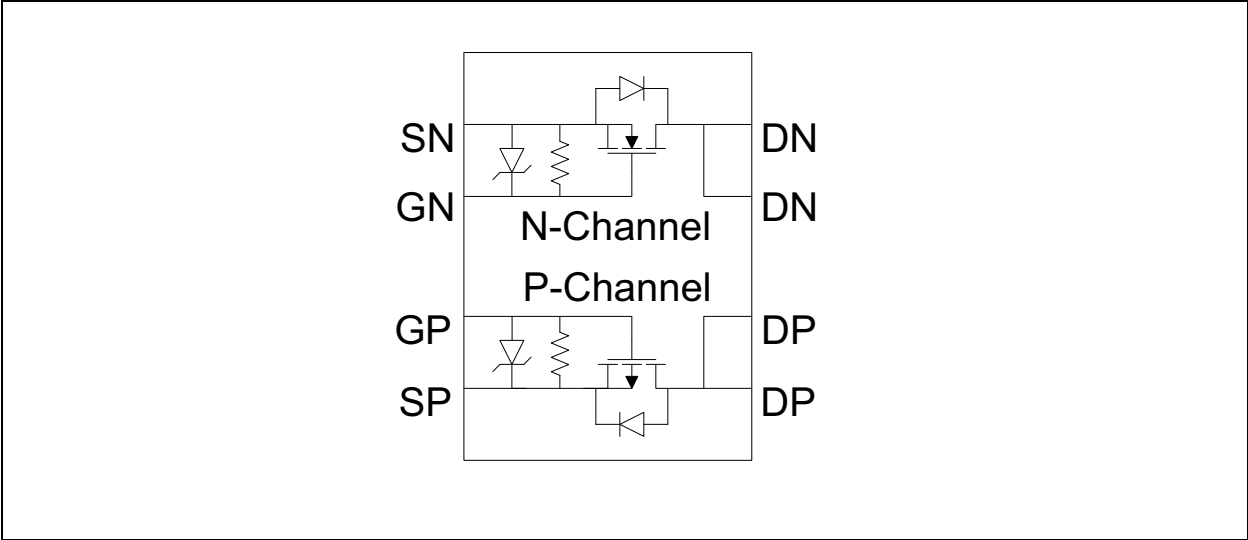
Package Types



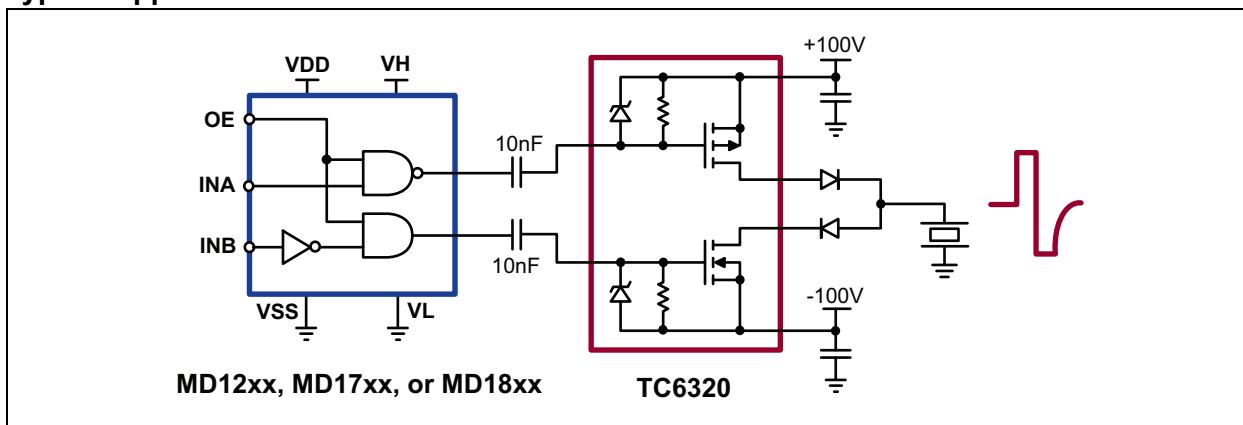
See [Table 2-1](#) and [Table 2-2](#) for pin information.

TC6320

Functional Block Diagram



Typical Application Circuit



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Drain-to-source Voltage	BV_{DSS}
Drain-to-gate Voltage	BV_{DGS}
Operating Ambient Temperature, T_A	-55°C to +150°C
Storage Temperature, T_S	-55°C to +150°C

† **Notice:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

N-CHANNEL ELECTRICAL CHARACTERISTICS

Electrical Specifications: $T_A = T_J = 25^\circ\text{C}$ unless otherwise specified.

Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
DC PARAMETER (Note 1 unless otherwise specified)						
Drain-to-source Breakdown Voltage	BV_{DSS}	200	—	—	V	$V_{GS} = 0V, I_D = 2\text{ mA}$
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2	V	$V_{GS} = V_{DS}, I_D = 1\text{ mA}$
Change in $V_{GS(th)}$ with Temperature	$\Delta V_{GS(th)}$	—	—	-4.5	mV/°C	$V_{GS} = V_{DS}, I_D = 1\text{ mA}$ (Note 2)
Gate-to-source Shunt Resistor	R_{GS}	10	—	50	kΩ	$I_{GS} = 100\text{ }\mu\text{A}$
Gate-to-Source Zener Voltage	V_{ZGS}	13.2	—	25	V	$I_{GS} = 2\text{ mA}$
Zero-gate Voltage Drain Current	I_{DSS}	—	—	10	μA	$V_{DS} = \text{Maximum rating}, V_{GS} = 0V$
		—	—	1	mA	$V_{DS} = 0.8 \text{ Maximum rating}, V_{GS} = 0V, T_A = 125^\circ\text{C}$ (Note 2)
On-state Drain Current	$I_{D(ON)}$	1	—	—	A	$V_{GS} = 4.5V, V_{DS} = 25V$
		2	—	—		$V_{GS} = 10V, V_{DS} = 25V$
Static Drain-to-source On-state Resistance	$R_{DS(ON)}$	—	—	8	Ω	$V_{GS} = 4.5V, I_D = 150\text{ mA}$
		—	—	7		$V_{GS} = 10V, I_D = 1A$
Change in $R_{DS(ON)}$ with Temperature	$\Delta R_{DS(ON)}$	—	—	1	%/°C	$V_{GS} = 4.5V, I_D = 150\text{ mA}$ (Note 2)
AC PARAMETER (Note 2)						
Forward Transconductance	G_{FS}	400	—	—	mmho	$V_{DS} = 25V, I_D = 500\text{ mA}$
Input Capacitance	C_{ISS}	—	—	110	pF	$V_{GS} = 0V,$ $V_{DS} = 25V,$ $f = 1\text{ MHz}$
Common Source Output Capacitance	C_{OSS}	—	—	60	pF	
Reverse Transfer Capacitance	C_{RSS}	—	—	23	pF	
Turn-on Delay Time	$t_{d(ON)}$	—	—	10	ns	$V_{DD} = 25V,$ $I_D = 1A,$ $R_{GEN} = 25\Omega$
Rise Time	t_r	—	—	15	ns	
Turn-off Delay Time	$t_{d(OFF)}$	—	—	20	ns	
Fall Time	t_f	—	—	15	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V_{SD}	—	—	1.8	V	$V_{GS} = 0V, I_{SD} = 500\text{ mA}$ (Note 1)
Reverse Recovery Time	t_{rr}	—	300	—	ns	$V_{GS} = 0V, I_{SD} = 500\text{ mA}$ (Note 2)

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 μs pulse, 2% duty cycle.

2: Specification is obtained by characterization and is not 100% tested.

P-CHANNEL ELECTRICAL CHARACTERISTICS

Electrical Specifications: T _A = T _J = 25°C unless otherwise specified.						
Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
DC PARAMETER (Note 1 unless otherwise specified)						
Drain-to-source Breakdown Voltage	BV _{DSS}	-200	—	—	V	V _{GS} = 0V, I _D = -2 mA
Gate Threshold Voltage	V _{GS(th)}	-1	—	-2.4	V	V _{GS} = V _{DS} , I _D = -1 mA
Change in V _{GS(th)} with Temperature	ΔV _{GS(th)}	—	—	4.5	mV/°C	V _{GS} = V _{DS} , I _D = -1 mA (Note 2)
Gate-to-source Shunt Resistor	R _{GS}	10	—	50	kΩ	I _{GS} = 100 μA
Gate-to-Source Zener Voltage	VZ _{GS}	13.2	—	25	V	I _{GS} = -2 mA
Zero-gate Voltage Drain Current	I _{DSS}	—	—	-10	μA	V _{DS} = Maximum rating, V _{GS} = 0V
		—	—	-1	mA	V _{DS} = 0.8 Maximum rating, V _{GS} = 0V, T _A = 125°C (Note 2)
On-state Drain Current	I _{D(ON)}	-1	—	—	A	V _{GS} = -4.5V, V _{DS} = -25V
		-2	—	—		V _{GS} = -10V, V _{DS} = -25V
Static Drain-to-source On-state Resistance	R _{DS(ON)}	—	—	10	Ω	V _{GS} = -4.5V, I _D = -150 mA
		—	—	8		V _{GS} = -10V, I _D = -1A
Change in R _{DS(ON)} with Temperature	ΔR _{DS(ON)}	—	—	1	%/°C	V _{GS} = -10V, I _D = -200 mA (Note 2)
AC PARAMETER (Note 2)						
Forward Transconductance	G _{FS}	400	—	—	mmho	V _{DS} = -25V, I _D = -500 mA
Input Capacitance	C _{ISS}	—	—	200	pF	V _{GS} = 0V, V _{DS} = -25V, f = 1 MHz
Common Source Output Capacitance	C _{OSS}	—	—	55	pF	
Reverse Transfer Capacitance	C _{RSS}	—	—	30	pF	
Turn-on Delay Time	t _{d(ON)}	—	—	10	ns	V _{DD} = -25V, I _D = -1A, R _{GEN} = 25Ω
Rise Time	t _r	—	—	15	ns	
Turn-off Delay Time	t _{d(OFF)}	—	—	20	ns	
Fall Time	t _f	—	—	15	ns	
DIODE PARAMETER						
Diode Forward Voltage Drop	V _{SD}	—	—	-1.8	V	V _{GS} = 0V, I _{SD} = -500 mA (Note 1)
Reverse Recovery Time	t _{rr}	—	300	—	ns	V _{GS} = 0V, I _{SD} = -500 mA (Note 2)

Note 1: All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 μs pulse, 2% duty cycle.

2: Specification is obtained by characterization and is not 100% tested.

TEMPERATURE SPECIFICATIONS

Electrical Characteristics: Unless otherwise specified, for all specifications $T_A = T_J = +25^\circ\text{C}$.						
Parameter	Sym.	Min.	Typ.	Max.	Unit	Conditions
TEMPERATURE RANGE						
Operating Ambient Temperature	T_A	-55	—	+150	$^\circ\text{C}$	
Storage Temperature	T_S	-55	—	+150	$^\circ\text{C}$	
PACKAGE THERMAL RESISTANCE						
8-lead VDFN	θ_{JA}	—	44	—	$^\circ\text{C/W}$	Note 1
8-lead SOIC	θ_{JA}	—	101	—	$^\circ\text{C/W}$	Note 1

Note 1: 1 oz., four-layer, 3" x 4" PCB

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2.0 PIN DESCRIPTION

Table 2-1 and Table 2-2 show the description of pins in TC6320 8-lead VDFN and 8-lead SOIC, respectively. Refer to [Package Types](#) for the location of pins.

TABLE 2-1: 8-LEAD VDFN PIN FUNCTION TABLE

Pin Number	Pin Name	Description
1	SN	Source N-channel
2	GN	Gate N-channel
3	GP	Gate P-channel
4	SP	Source P-channel
5	DP	Drain P-channel
6	DP	Drain P-channel
7	DN	Drain N-channel
8	DN	Drain N-channel

TABLE 2-2: 8-LEAD SOIC FUNCTION TABLE

Pin Number	Pin Name	Description
1	SN	Source N-channel
2	GN	Gate N-channel
3	SP	Source P-channel
4	GP	Gate P-channel
5	DP	Drain P-channel
6	DP	Drain P-channel
7	DN	Drain N-channel
8	DN	Drain N-channel

3.0 FUNCTIONAL DESCRIPTION

Figure 3-1 and Figure 3-2 illustrate the switching waveforms and test circuits for TC6320.

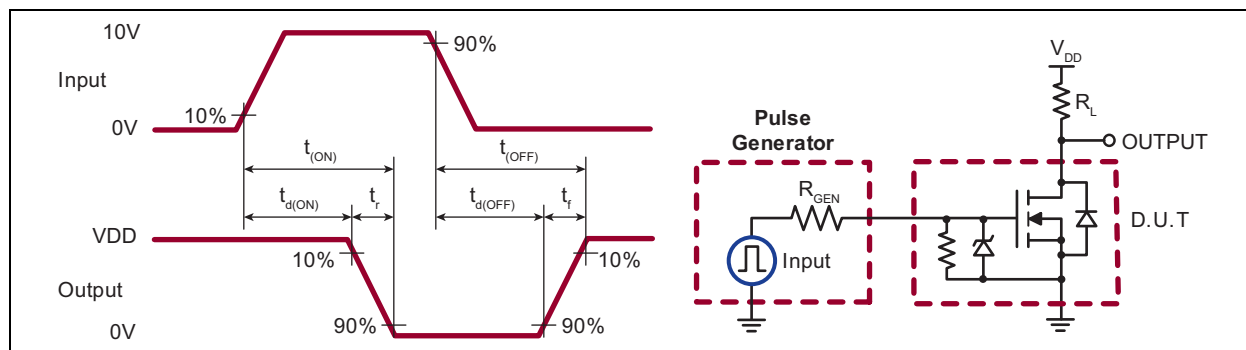


FIGURE 3-1: N-Channel Switching Waveforms and Test Circuit.

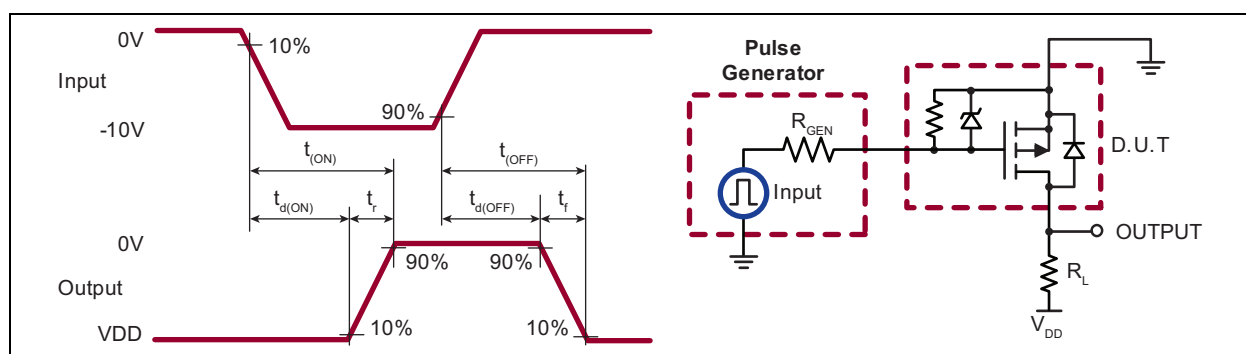


FIGURE 3-2: P-Channel Switching Waveforms and Test Circuit.

PRODUCT SUMMARY

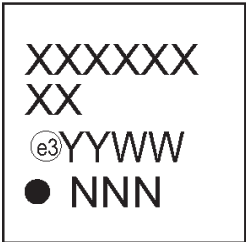
BV_{DSS}/BV_{DGS} (V)		$R_{DS(ON)}$ (Maximum) (Ω)	
N-Channel	P-Channel	N-Channel	P-Channel
200	-200	7	8

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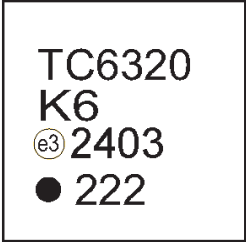
4.0 PACKAGING INFORMATION

4.1 Package Marking Information

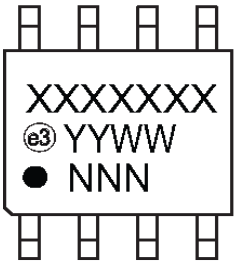
8-lead VDFN



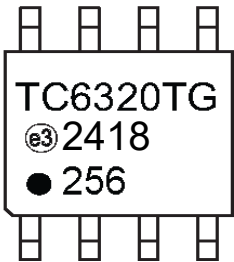
Example



8-lead SOIC



Example

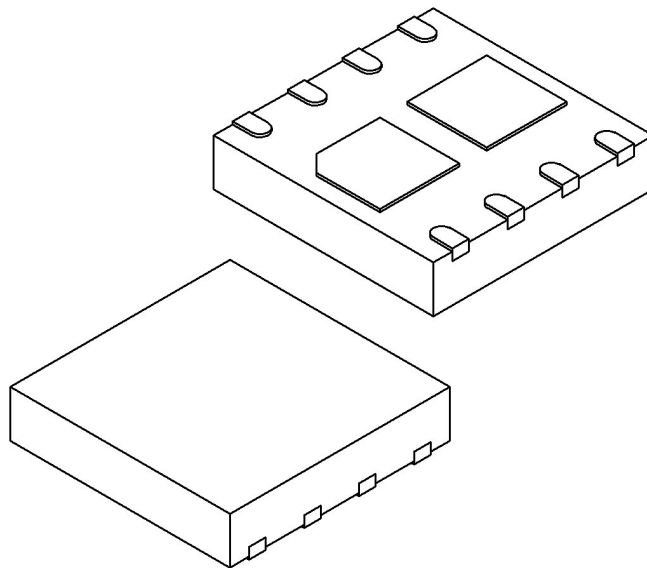


Legend:	XX...X	Product Code or Customer-specific information
	Y	Year code (last digit of calendar year)
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code
	e3	Pb-free JEDEC® designator for Matte Tin (Sn)
	*	This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.
Note:	In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. The package may or not include the corporate logo.	

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8-Lead Very Thin Plastic Quad Flat, No Lead Package (8RX) - 4x4x0.9 mm Body [VQFN] With Dual 1.45mm Exposed Pads

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Terminals	N	8		
Pitch	e	1.00 BSC		
Overall Height	A	0.80	0.85	0.90
Standoff	A1	0.00	–	0.05
Terminal Thickness	A3	0.20 REF		
Overall Length	D	4.00 BSC		
Exposed Pad Length (X2)	D2	1.35	1.45	1.55
Overall Width	E	4.00 BSC		
Exposed Pad Width (X2)	E2	1.35	1.45	1.55
Terminal Width	b	0.25	0.30	0.35
Terminal Length	L	0.40	0.50	0.60
Exposed Pad to Exposed Pad	K1	0.50 REF		
Terminal to Exposed Pad	K2	0.775 REF		

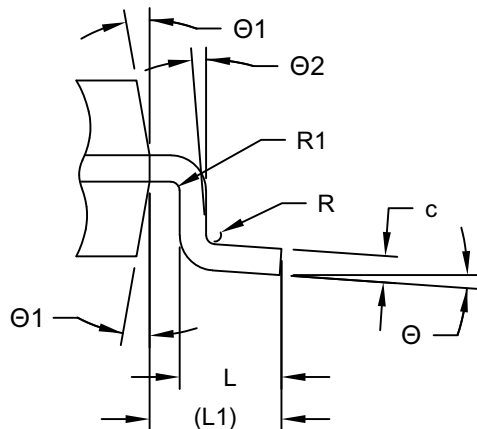
Notes:

- Pin 1 visual index feature may vary but must be located within the hatched area.
- Package is saw singulated.
- Dimensioning and tolerancing per ASME Y14.5M
BSC: Basic Dimension. Theoretically exact value shown without tolerances.
REF: Reference Dimension, usually without tolerance, for information purposes only.

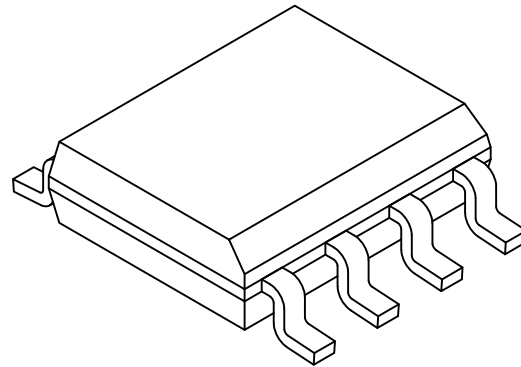
Microchip Technology Drawing C04-285 Rev A Sheet 2 of 2

8-Lead Small Outline Integrated Circuit (4CX) - 3.90 mm Body [SOIC] Supertex Legacy Package TG

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



VIEW C



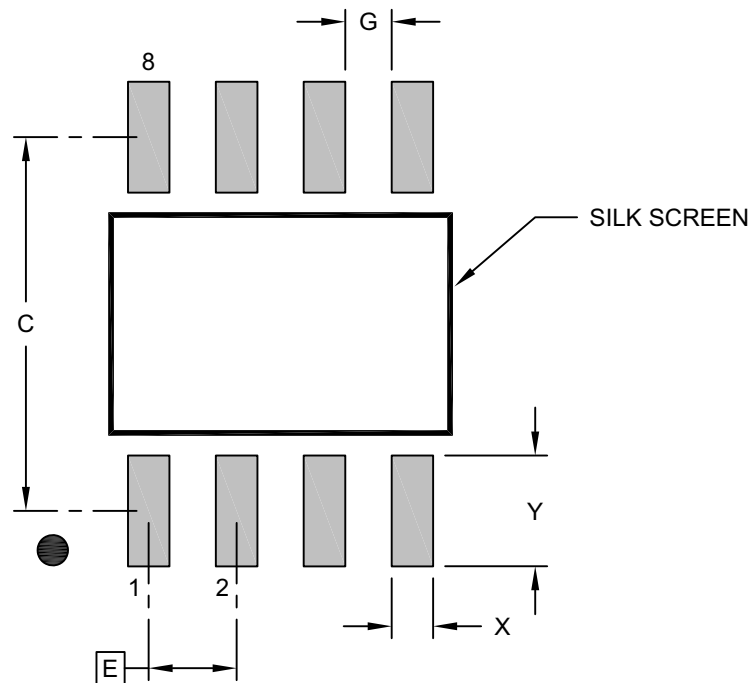
Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Terminals	N	8		
Pitch	e	1.27 BSC		
Overall Height	A	1.35	-	1.75
Standoff	A1	0.10	-	0.25
Molded Package Height	A2	1.25	-	1.65
Overall Length	D	4.90 BSC		
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Index Chamfer	h	0.25	-	0.50
Terminal Width	b	0.31	0.41	0.51
Terminal Thickness	c	0.17	-	0.25
Terminal Length	L	0.40	-	1.00
Footprint	L1	1.04 REF		
Terminal Bend Radius	R	0.07	-	-
Terminal Bend Radius	R1	0.07	-	-
Lead Angle	Θ	0°	-	8°
Mold Draft Angle	Θ1	5°	-	15°
Lead Angle	Θ2	0°	-	-

Notes:

- Pin 1 visual index feature may vary, but must be located within the hatched area.
- Dimensioning and tolerancing per ASME Y14.5M
BSC: Basic Dimension. Theoretically exact value shown without tolerances.
REF: Reference Dimension, usually without tolerance, for information purposes only.

8-Lead Small Outline Integrated Circuit (4CX) - 3.90 mm (.150 In.) Body [SOIC] Supertex Legacy Package TG

Note: For the most current package drawings, please see the Microchip Packaging Specification located at <http://www.microchip.com/packaging>



RECOMMENDED LAND PATTERN

Dimension Limits	Units	MILLIMETERS		
		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Contact Pad Spacing	C		5.40	
Contact Pad Width (Xnn)	X			0.60
Contact Pad Length (Xnn)	Y			1.60
Contact Pad to Contact Pad (Xnn)	G	0.67		

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2267 Rev A

APPENDIX A: REVISION HISTORY

Revision B (June 2024)

- Modified [Section “Package Types”](#) from 5-lead DFN to 8-lead VDFN.
- Updated [Section 4.1 “Package Marking Information”](#) with the latest Package Drawings.

Revision A (October 2017)

- Converted Supertex Doc# DSFP-TC6320 to Microchip DS20005697A.
- Changed the package marking format.
- Changed the quantity of the 8-lead DFN K6 package from 3000/Reel to 3300/Reel.
- Changed the quantity of the 8-lead SOIC TG package from 2000/Reel to 3300/Reel.
- Minor text changes throughout the document.

TC6320

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

<u>PART NO.</u>					
Device	Package Options		Environmental		Media Type
Device:	TC6320	=	N-Channel and P-Channel Enhancement-Mode MOSFET Pair		
Packages:	K6	=	8-lead (4x4) VDFN		
	TG	=	8-lead SOIC		
Environmental:	G	=	Lead (Pb)-free/RoHS-compliant Package		
Media Type:	(blank)	=	3300/Reel for a K6 Package		
		=	3300/Reel for a TG Package		

Examples:

a) TC6320K6-G: N-Channel and P-Channel Enhancement-Mode MOSFET Pair, 8-lead (4x4) VDFN, 3300/Reel

b) TC6320TG-G: N-Channel and P-Channel Enhancement-Mode MOSFET Pair, 8-lead SOIC, 3300/Reel

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India - Pune
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Japan - Osaka
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Japan - Tokyo
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Korea - Daegu
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Malaysia - Penang
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Philippines - Manila
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Taiwan - Hsin Chu
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Taiwan - Kaohsiung
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Vietnam - Ho Chi Minh
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Israel - Hod Hasharon
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